

HAT2254R

Silicon N Channel Power MOSFET Power Switching

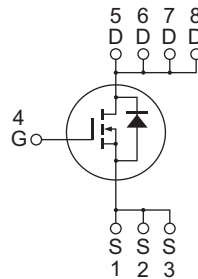
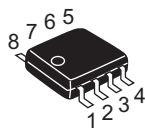
R07DS1367EJ0101
Rev.1.01
Jan 20, 2017

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 7.2 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8<FP-8DAV>)



1, 2, 3 Source
4 Gate
5, 6, 7, 8 Drain

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	14	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	112	A
Body-drain diode reverse drain current	I_{DR}	14	A
Avalanche current	I_{AP} ^{Note 2}	14	A
Avalanche energy	E_{AR} ^{Note 2}	19.6	mJ
Channel dissipation	P_{ch} ^{Note 3}	2.5	W
Channel to ambient thermal impedance	θ_{ch-a} ^{Note 3}	50	$^\circ\text{C}/\text{W}$
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$
 2. Value at $T_{ch} = 25^\circ\text{C}$, $R_g \geq 50 \Omega$
 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10\text{s}$

Electrical Characteristics

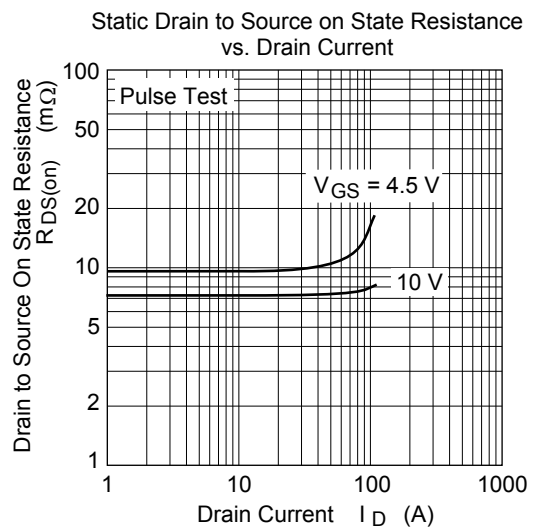
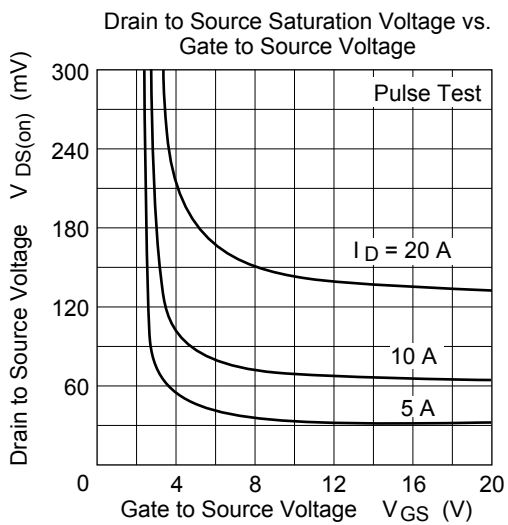
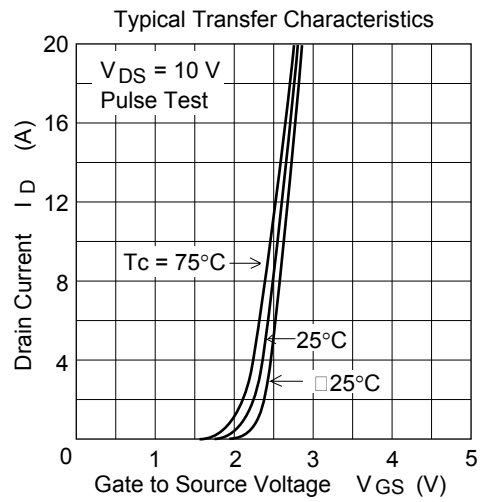
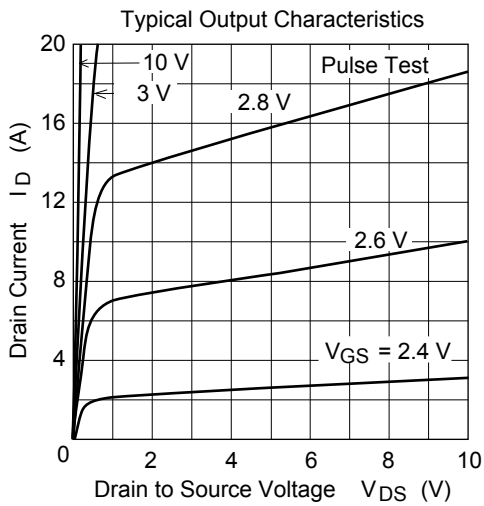
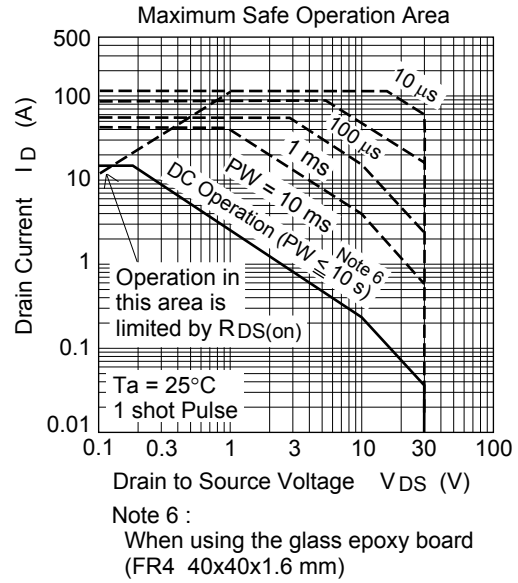
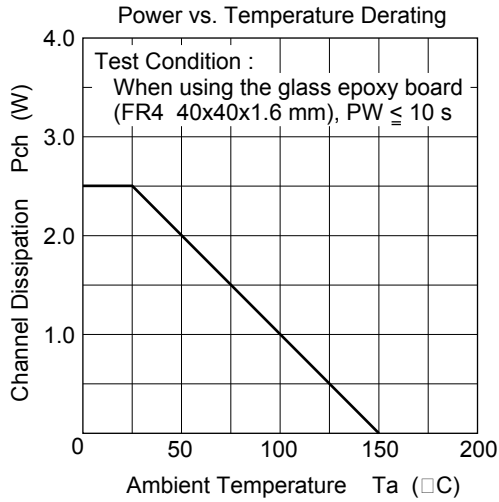
(Ta = 25°C)

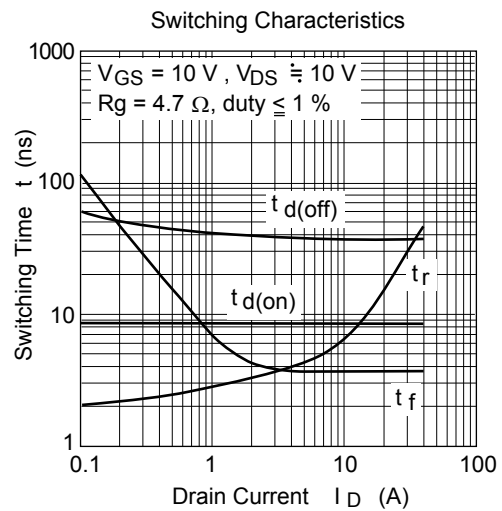
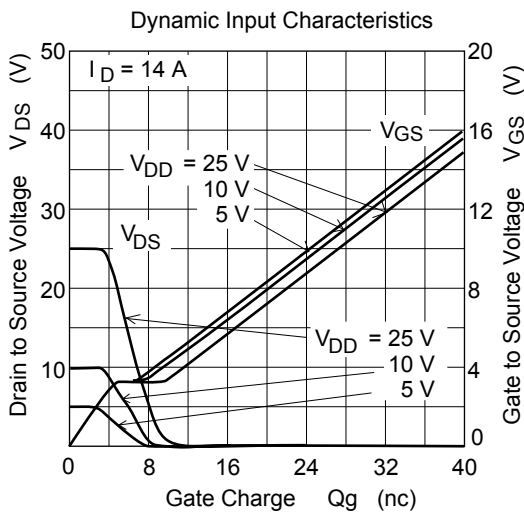
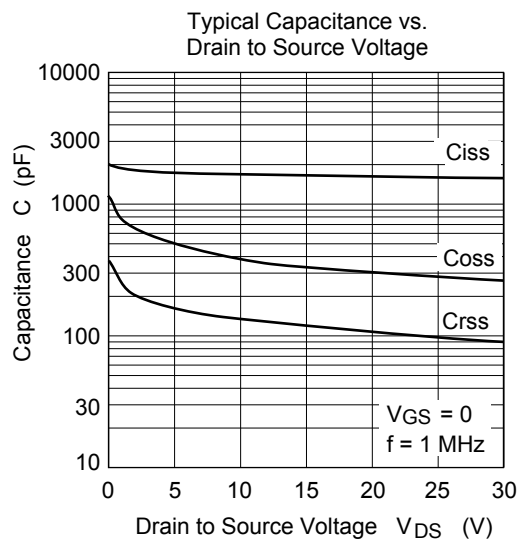
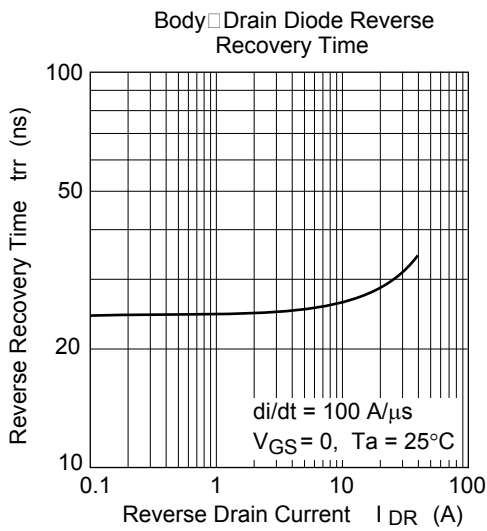
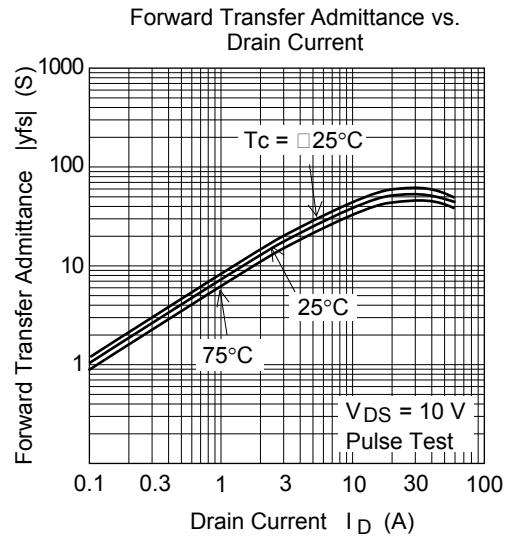
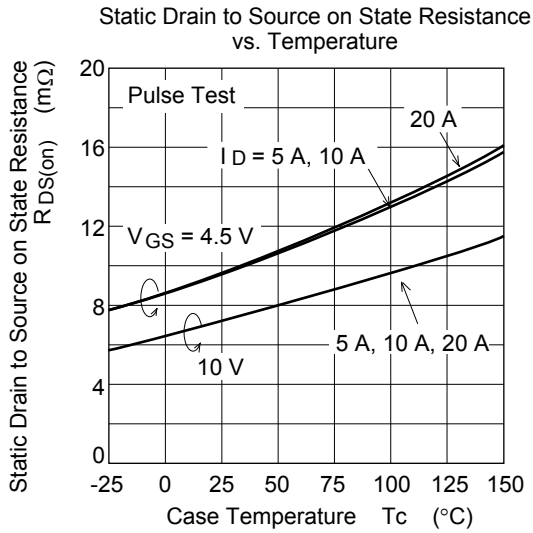
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	7.2	9.0	$\text{m}\Omega$	$I_D = 7 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
resistance	$R_{DS(on)}$	—	9.6	14.0	$\text{m}\Omega$	$I_D = 7 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	18	30	—	S	$I_D = 7 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	1700	3400	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	390	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	135	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g ^{Note5}	0.8	1.3	4.0	Ω	
Total gate charge	Q_g	—	11	—	nc	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	4.7	—	nc	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	2.5	—	nc	$I_D = 14 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	8.5	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 7 \text{ A}$
Rise time	t_r	—	5	—	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	38	—	ns	$R_L = 1.42 \Omega$
Fall time	t_f	—	3.8	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.80	1.04	V	$I_F = 14 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	28	56	ns	$I_F = 14 \text{ A}$, $V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$
Body-drain diode reverse recovery charge	Q_{rr}	—	25	50	nC	

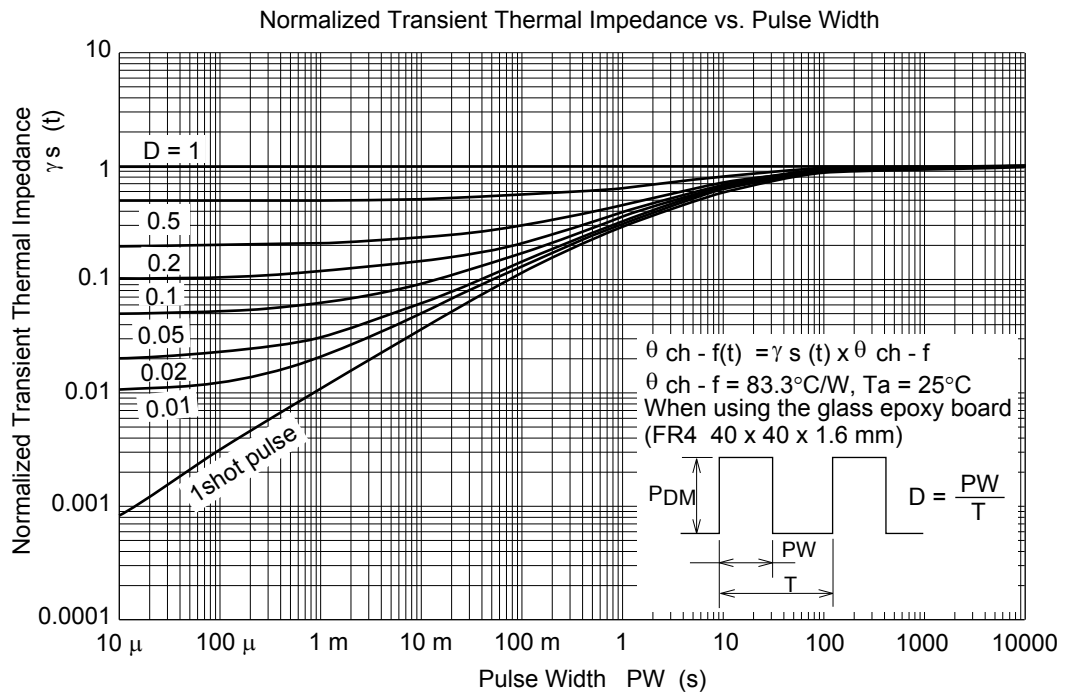
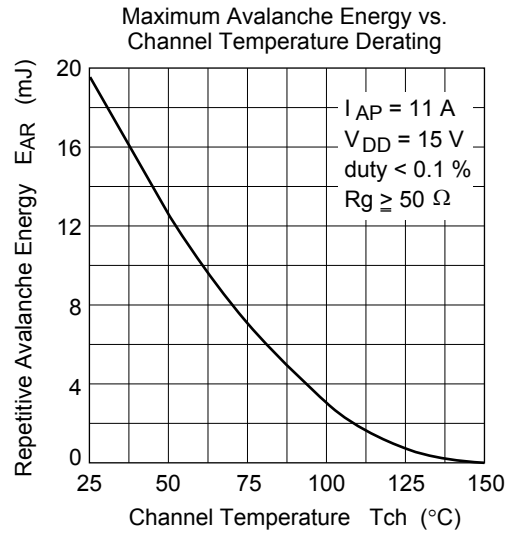
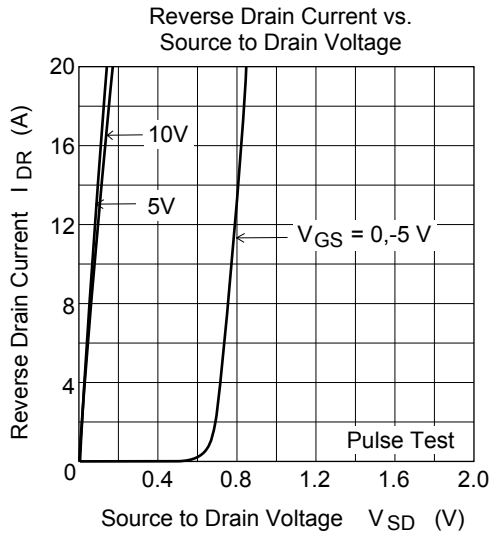
Notes: 4. Pulse test

5. Screening test performed on wafer

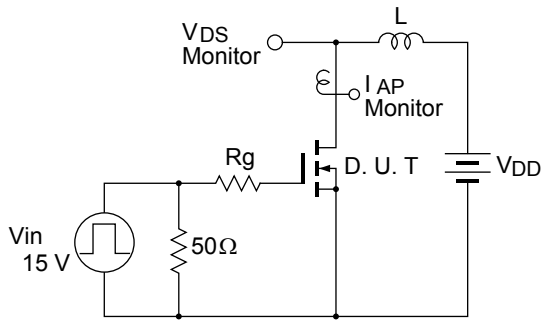
Main Characteristics





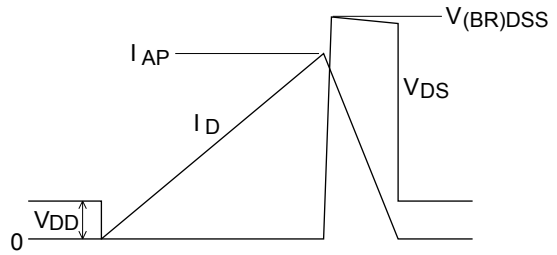


Avalanche Test Circuit

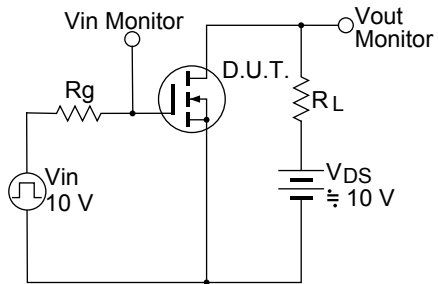


Avalanche Waveform

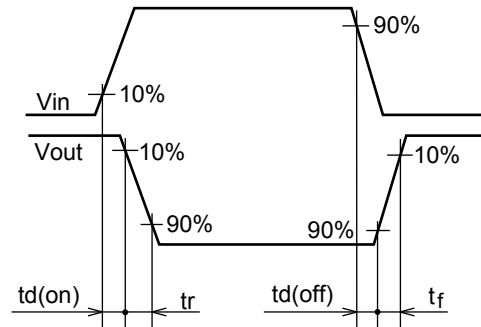
$$E_{AR} = \frac{1}{2} L I_{AP}^2 \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



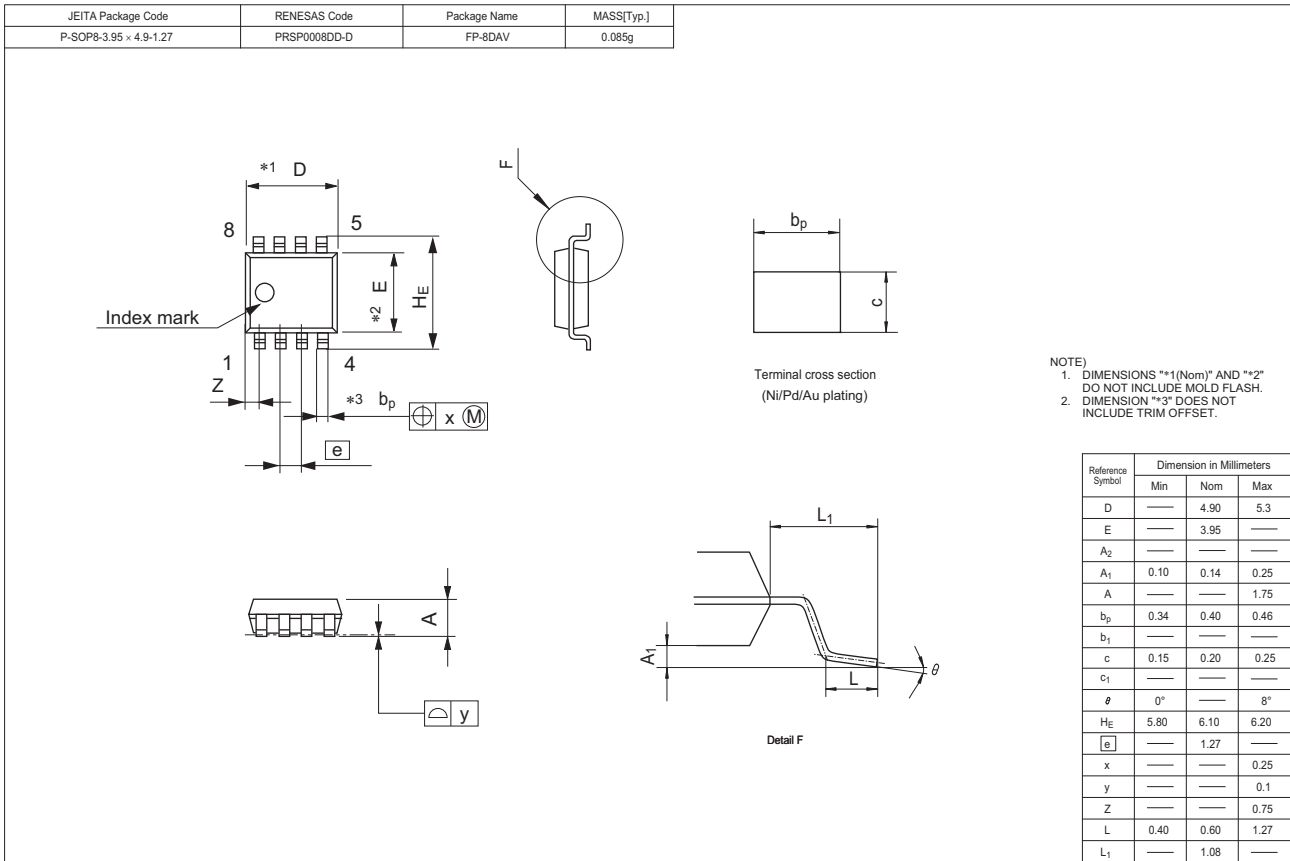
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
HAT2254R-EL-E	2500 pcs	Taping

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2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
3251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, UK
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics GmbH
Arcadistraße 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhichunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0899

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-8888, Fax: +852-2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

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Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jin Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7855-9300, Fax: +60-3-7855-9510

Renesas Electronics India Pvt. Ltd.
No. 777C, 100 Feet Road, HAL, Sige, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141